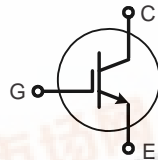




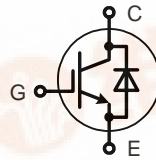
IXEH 40N120
IXEH 40N120D1

NPT³ IGBT

I_{C25} = 60 A
V_{CEs} = 1200 V
V_{CE(sat)typ.} = 2.4 V

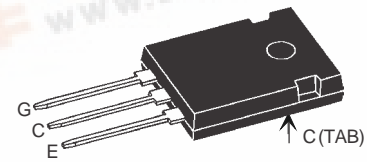


IXEH 40N120



IXEH 40N120D1

TO-247 AD



IGBT

Symbol	Conditions	Maximum Ratings	
V _{CEs}	T _{VJ} = 25°C to 150°C	1200	V
V _{GES}		± 20	V
I _{C25}	T _C = 25°C	60	A
I _{C90}	T _C = 90°C	40	A
I _{CM} V _{CEK}	V _{GE} = ±15 V; R _G = 39 Ω; T _{VJ} = 125°C RBSOA, Clamped inductive load; L = 100 μH	50	A
t _{SC} (SCSOA)	V _{CE} = 900V; V _{GE} = ±15 V; R _G = 39 Ω; T _{VJ} = 125°C non-repetitive	10	μs
P _{tot}	T _C = 25°C	300	W

Features

- NPT³ IGBT
 - low saturation voltage
 - positive temperature coefficient for easy paralleling
 - fast switching
 - short tail current for optimized performance in resonant circuits
- optional HiPerFRED™ diode
 - fast reverse recovery
 - low operating forward voltage
 - low leakage current
- TO-247 package
 - industry standard outline
 - epoxy meets UL 94V-0

Applications

- AC drives
- DC drives and choppers
- Uninterruptible power supplies (UPS)
- switched-mode and resonant-mode power supplies
- inductive heating, cookers

Symbol	Conditions	Characteristic Values (T _{VJ} = 25°C, unless otherwise specified)			
		min.	typ.	max.	
V _{CE(sat)}	I _C = 40 A; V _{GE} = 15 V; T _{VJ} = 25°C T _{VJ} = 125°C	2.4	3.0	V	
V _{GE(th)}	I _C = 1 mA; V _{CE} = V _{CE}	4.5	6.5	V	
I _{CEs}	V _{CE} = V _{CEs} ; V _{GE} = 0 V; T _{VJ} = 25°C T _{VJ} = 125°C	0.4	0.4	mA	
I _{GES}	V _{CE} = 0 V; V _{GE} = ± 20 V		200	nA	
t _{d(on)} t _r t _{d(off)} t _f E _{on} E _{off}	Inductive load, T _{VJ} = 125°C V _{CE} = 600 V; I _C = 40 A V _{GE} = ±15 V; R _G = 39 Ω	85	50	ns	
		440	50	ns	
		6.1	3.0	mJ	
		3.0		mJ	
C _{ies}		V _{CE} = 25 V; V _{GE} = 0 V; f = 1 MHz	2		nF
Q _{Gon}		V _{CE} = 600 V; V _{GE} = 15 V; I _C = 25 A	250		nC
R _{thJC}			0.42	KW	



Diode [D1 version only]

Symbol	Conditions	Maximum Ratings	
I_{F25}	$T_C = 25^\circ\text{C}$	60	A
I_{F90}	$T_C = 90^\circ\text{C}$	35	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_F	$I_F = 40\text{ A}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	2.6 2.0		V V
I_{RM} t_{rr} $E_{rec(off)}$	$I_F = 30\text{ A}; di_F/dt = -500\text{ A}/\mu\text{s}; T_{VJ} = 125^\circ\text{C}$ $V_R = 600\text{ V}; V_{GE} = 0\text{ V}$	51		A
		180		ns
		1.8		mJ
R_{thJC}				1.0 KW

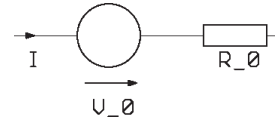
Component

Symbol	Conditions	Maximum Ratings	
T_{VJ}		-55...+150	$^\circ\text{C}$
T_{stg}		-55...+150	$^\circ\text{C}$
M_d	mounting torque	0.8...1.2	Nm

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
R_{thCH}	with heatsink compound		0.25	KW
Weight			6	g

Equivalent Circuits for Simulation

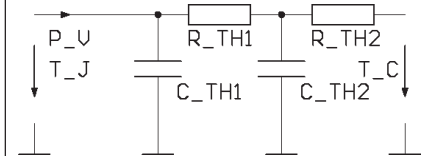
Conduction



IGBT (typ. at $V_{GE} = 15\text{ V}; T_J = 125^\circ\text{C}$)
 $V_0 = 0.95\text{ V}; R_0 = 45\text{ m}\Omega$

Diode (typ. at $T_J = 125^\circ\text{C}$)
 $V_0 = 1.26\text{ V}; R_0 = 15\text{ m}\Omega$

Thermal Response



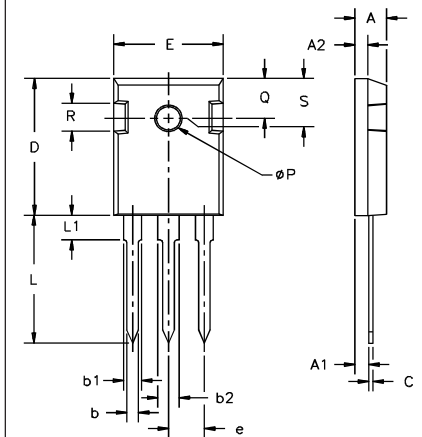
IGBT

$C_{th1} = 0.007\text{ J/K}; R_{th1} = 0.215\text{ K/W}$
 $C_{th2} = 0.187\text{ J/K}; R_{th2} = 0.205\text{ K/W}$

Diode

$C_{th1} = 0.006\text{ J/K}; R_{th1} = 0.649\text{ K/W}$
 $C_{th2} = 0.113\text{ J/K}; R_{th2} = 0.351\text{ K/W}$

TO-247 AD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

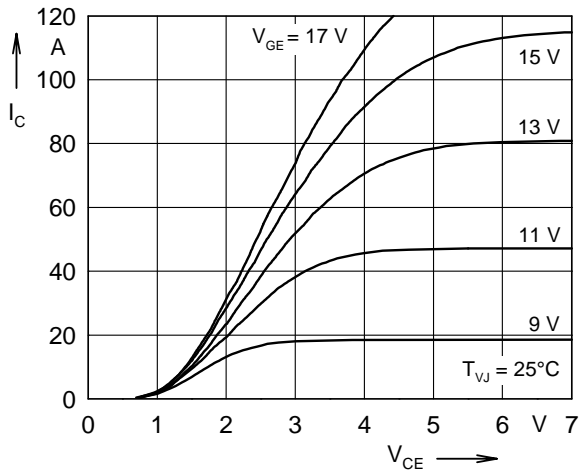


Fig. 1 Typ. output characteristics

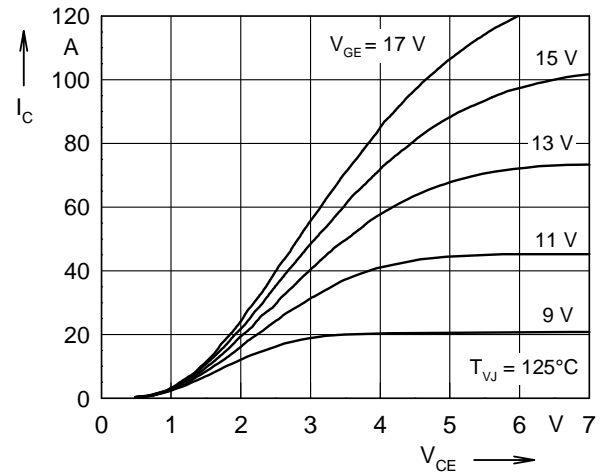


Fig. 2 Typ. output characteristics

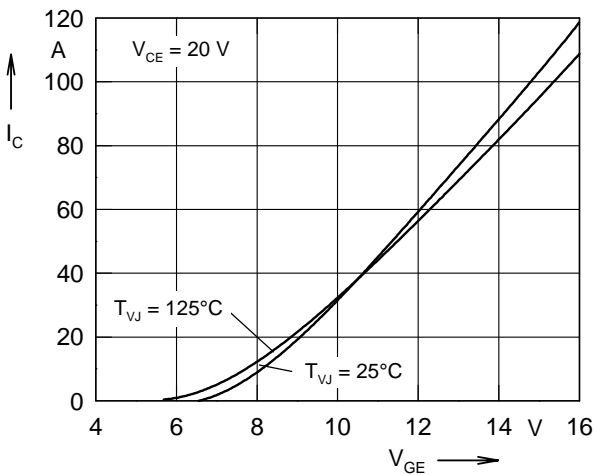


Fig. 3 Typ. transfer characteristics

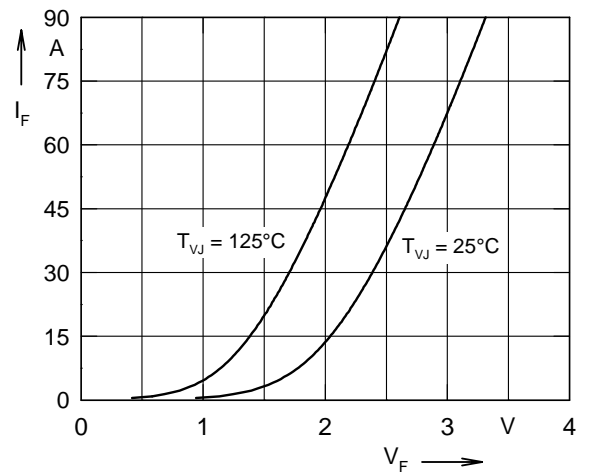


Fig. 4 Typ. forward characteristics of free wheeling diode

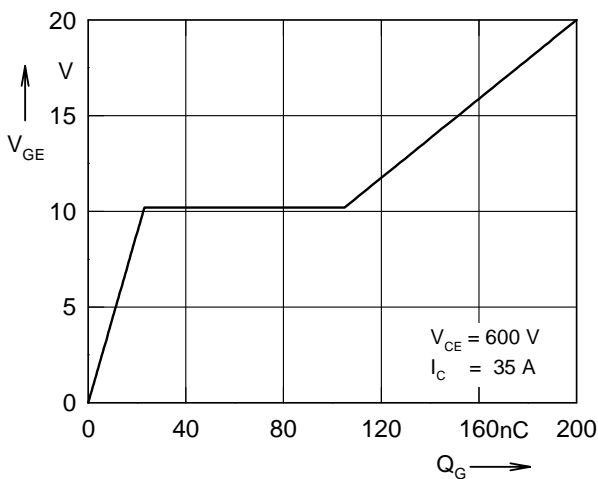


Fig. 5 Typ. turn on gate charge

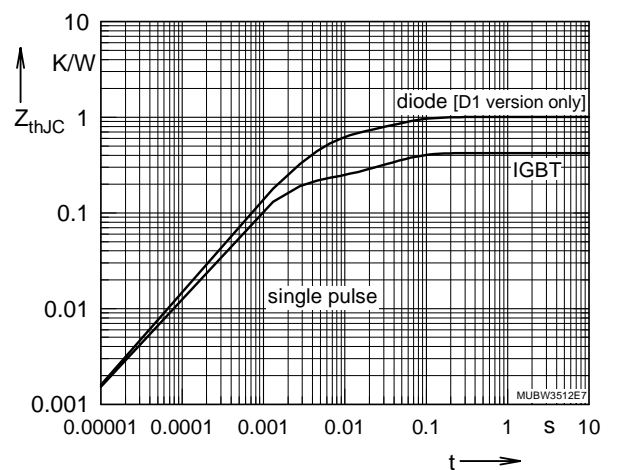


Fig. 6 Typ. transient thermal impedance

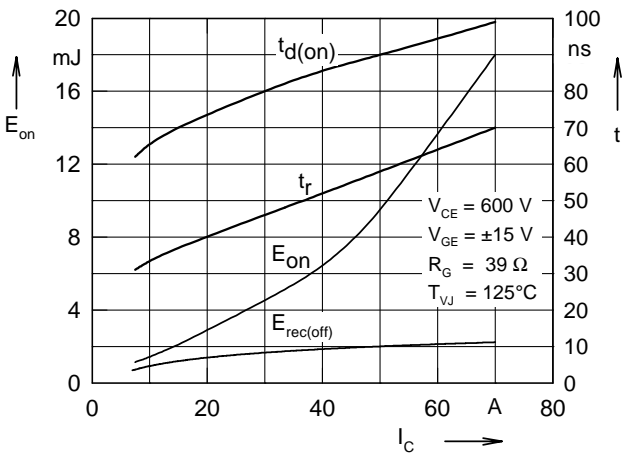


Fig. 7 Typ. turn on energy and switching times versus collector current

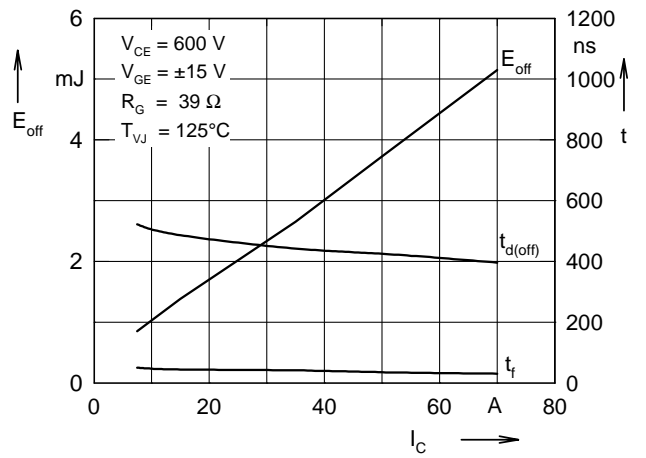


Fig. 8 Typ. turn off energy and switching times versus collector current

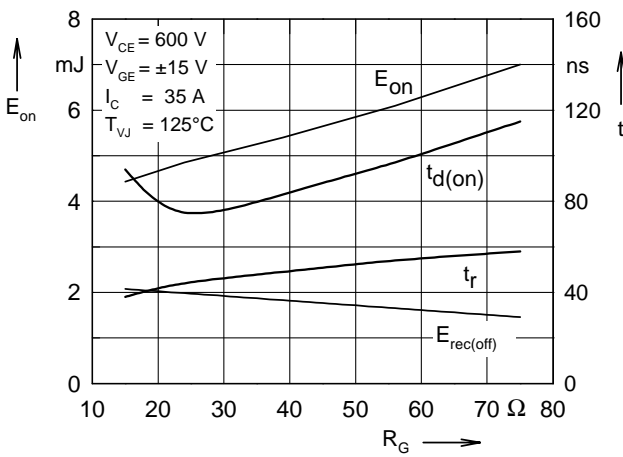


Fig. 9 Typ. turn on energy and switching times versus gate resistor

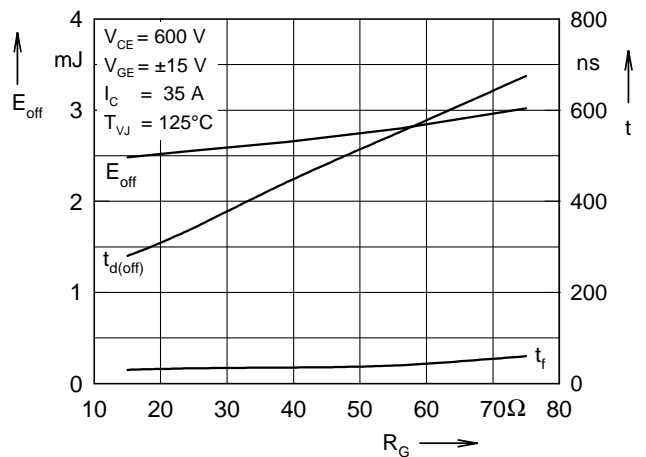


Fig. 10 Typ. turn off energy and switching times versus gate resistor

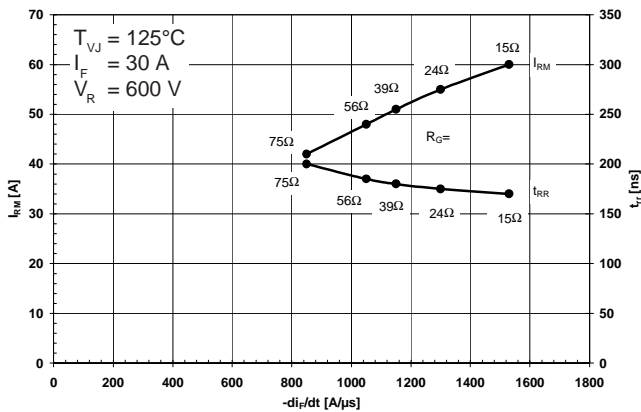


Fig. 11 Typ. turn off characteristics of free wheeling diode

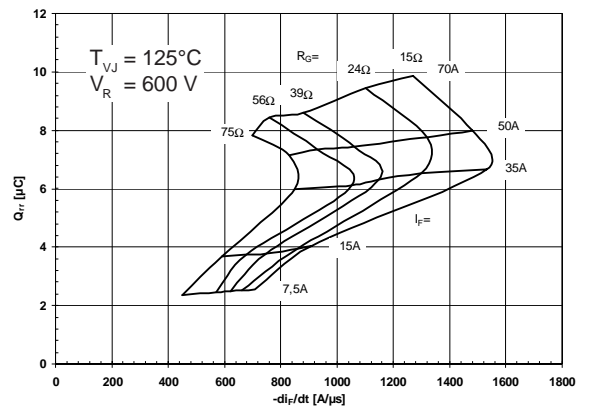


Fig. 12 Typ. turn off characteristics of free wheeling diode